EECS150 - Digital Design
Lecture 17 – Memory 2

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SDRAM Recap

- General Characteristics
  - Optimized for high density and therefore low cost/bit
  - Special fabrication process – DRAM rarely merged with logic circuits.
  - Needs periodic refresh (in most applications)
  - Relatively slow because:
    - High capacity leads to large cell arrays with high word- and bit-line capacitance
    - Complex read/write cycle. Read needs “precharge” and write-back
  - Multiple clock cycles per read or write access
  - Multiple reads and writes are often grouped together to amortize overhead. Referred to as “bursting”.
SDRAM Details

- Multiple “banks” of cell arrays are used to reduce access time:
  - Each bank is 4K rows by 512 “columns” by 16 bits (for our part)
- Read and Write operations as split into RAS (row access) followed by CAS (column access)
- These operations are controlled by sending commands
  - Commands are sent using the RAS, CAS, CS, & WE pins.
- Address pins are “time multiplexed”
  - During RAS operation, address lines select the bank and row
  - During CAS operation, address lines select the column.
- “ACTIVE” command “opens” a row for operation
  - Transfers the contents of the entire row to a row buffer
- Subsequent “READ” or “WRITE” commands modify the contents of the row buffer.
- For burst reads and writes during “READ” or “WRITE” the starting address of the block is supplied.
  - Burst length is programmable as 1, 2, 4, 8 or a “full page” (entire row) with a burst terminate option.
- Special commands are used for initialization (burst options etc.)
- A burst operation takes $\approx 4 + n$ cycles (for n words)
READ burst (with auto precharge)
WRITE burst (with auto precharge)

See datasheet for more details. Verilog simulation models available.
First-in-first-out (FIFO) Memory

• Used to implement *queues*.
• These find common use in computers and communication circuits.
• Generally, used for rate matching data producer and consumer:

  **stating state**

  ![Diagram of FIFO memory in stating state]

  **after write**

  ![Diagram of FIFO memory after write]

  **after read**

  ![Diagram of FIFO memory after read]

• Producer can perform many writes without consumer performing any reads (or vice versa). However, because of finite buffer size, on average, need equal number of reads and writes.
• Typical uses:
  – interfacing I/O devices.
    Example network interface. Data bursts from network, then processor bursts to memory buffer (or reads one word at a time from interface). Operations not synchronized.
  – Example: Audio output.
    Processor produces output samples in bursts (during process swap-in time). Audio DAC clocks it out at constant sample rate.
FIFO Interfaces

- After write or read operation, FULL and EMPTY indicate status of buffer.
- Used by external logic to control own reading from or writing to the buffer.
- FIFO resets to EMPTY state.
- HALF FULL (or other indicator of partial fullness) is optional.

Address pointers are used internally to keep next write position and next read position into a dual-port memory.

- If pointers equal after write $\Rightarrow$ FULL:

- If pointers equal after read $\Rightarrow$ EMPTY:
FIFO Implementation Details

- Assume, dual-port memory with asynchronous read, synchronous write.
- Binary counter for each of read and write address. CEs controlled by WE and RE.
- Equal comparator to see when pointers match.
- Flip-flop each for FULL and EMPTY flags:

<table>
<thead>
<tr>
<th>WE RD equal</th>
<th>EMPTY&lt;sub&gt;i&lt;/sub&gt;</th>
<th>FULL&lt;sub&gt;i&lt;/sub&gt;</th>
</tr>
</thead>
<tbody>
<tr>
<td>0 0 0</td>
<td>0</td>
<td>0</td>
</tr>
<tr>
<td>0 0 1</td>
<td>EMPTY&lt;sub&gt;i-1&lt;/sub&gt;</td>
<td>FULL&lt;sub&gt;i-1&lt;/sub&gt;</td>
</tr>
<tr>
<td>0 1 0</td>
<td>0</td>
<td>0</td>
</tr>
<tr>
<td>0 1 1</td>
<td>1</td>
<td>0</td>
</tr>
<tr>
<td>1 0 0</td>
<td>0</td>
<td>0</td>
</tr>
<tr>
<td>1 0 1</td>
<td>0</td>
<td>1</td>
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<tr>
<td>1 1 0</td>
<td>0</td>
<td>0</td>
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<td>EMPTY&lt;sub&gt;i-1&lt;/sub&gt;</td>
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</tr>
</tbody>
</table>

- Control logic with truth-table shown to left.
Xilinx BlockRam Versions

- Our simple version has latency problems.
  - FULL and EMPTY signals are asserted near the end of the clock period.
- Xilinx version solves this by “predicting” when full or empty will be asserted on next write/read operation. Also uses BlockRam with synchronous reads.
- Available on Xilinx website along with “app note” – application note. These are linked to our page.
- Two versions available. Easy to modify to change the width if necessary.
- Will use the “cc” (common clock) version for checkpoint 2.
- Can use the “ic” (independent clock) version later for bridging video camera to display.

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